

Products

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Power Matters.

Home ▶ 2N4003 (#23187)

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Product Status

Obsolete

Related Links

Technical support

How to Buy

Available Stock

Sales Contacts

Overview

Diagrams

Electrical Rating	Symbol	Min	Тур	Max	Unit
Collector to Emitter Saturation Voltage	V _{CE(sat)}			1.20	V
DC Current Gain	HFE	20.00		80.00	

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			120.00	V
Collector Current (dc)	I _C			30.00	А
Collector-Emitter Voltage (Base Open)	V _{CEO}			100.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			8.00	V
Power Dissipation, Total	P _T			100.00	W

This part can be found in the following product categories:

▶ Power Discretes & Modules ▶ BJT(BiPolar Junction Transistor) ▶ PNP Transistor

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